

/ Descriptions

TO-220 N
N-CHANNEL MOSFET in a TO-220 Plastic Package.

/ Features

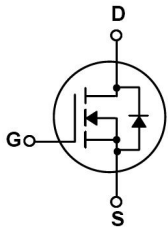
Ultra Low On-Resistance,fast switching.

/ Applications

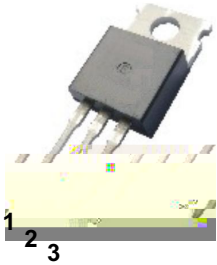
PFC

These devices are well suited for high efficient switched mode power supplies, Active power factor correction, electronic lamp ballast based on half bridge topology.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 4 D PIN 3 S

/ h_{FE} Classifications & Marking

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See Marking Instructions.



/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DSS}	85	V	
Drain Current	$I_D(Tc=25^{\circ}C)$	70	A	
Pulsed Drain Current	I_{DM}	245	A	
Gate-Source Voltage	V_{GS}	± 20	V	
Single Pulsed Avalanche Energy L=0.5mH	E_{AS}	238	mJ	
Avalanche Current	I_{AS}	75	A	
Total Power Dissipation	$P_D(Tc=25^{\circ}C)$	139	W	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^{\circ}C$	
Thermal Resistance-Junction to Ambient	$t \leq 10s$	$R_{\theta JA}$	$^{\circ}C/W$	
Thermal Resistance-Junction to Ambient	Steady-State			15
Thermal Resistance-Junction to Case	Steady-State			60
		$R_{\theta JC}$	0.9	

/ Electrical Characteristics(Ta=25)

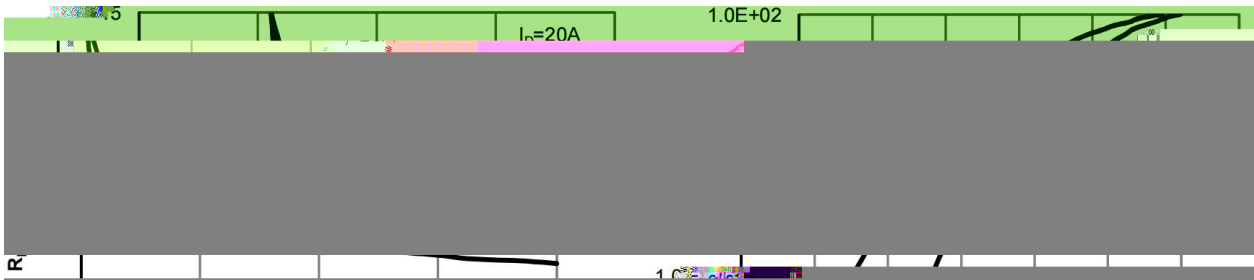
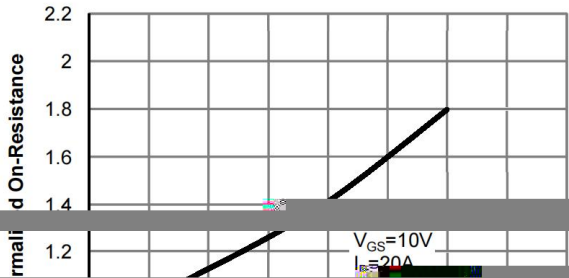
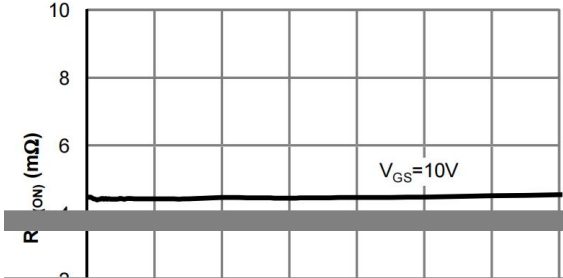
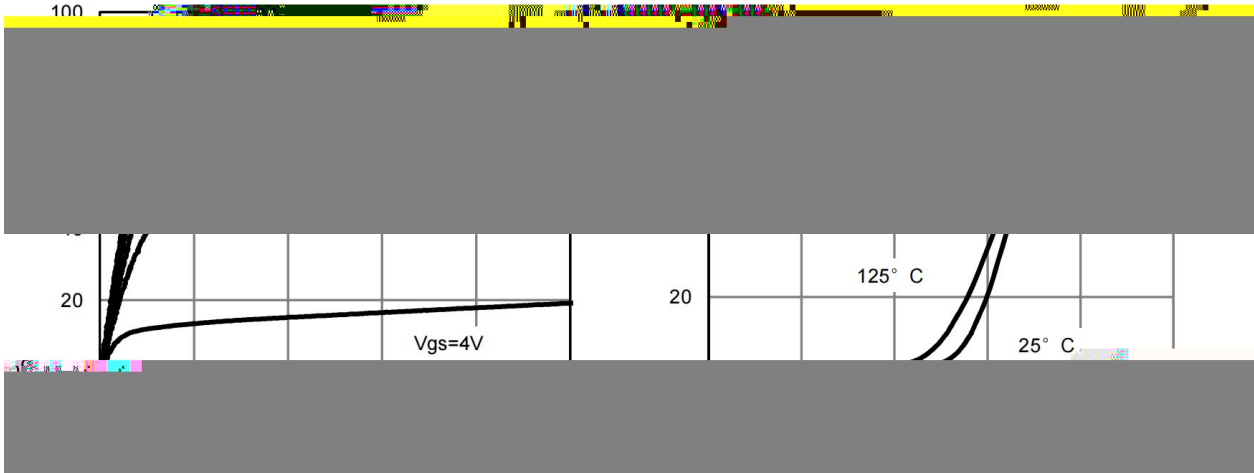
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	85			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=85V$ $V_{GS}=0V$			1	μA
		$T_J=125^{\circ}C$			5	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2	3	4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=70A$		4.5	5	m Ω
Forward On Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1A$			1.2	V
Input Capacitance	C_{iss}	$V_{DS}=40V$ $V_{GS}=0V$ $f=1MHz$		2900		pF
Output Capacitance	C_{oss}			750		
Reverse Transfer Capacitance	C_{rss}			15		



/ Electrical Characteristics(Ta=25)

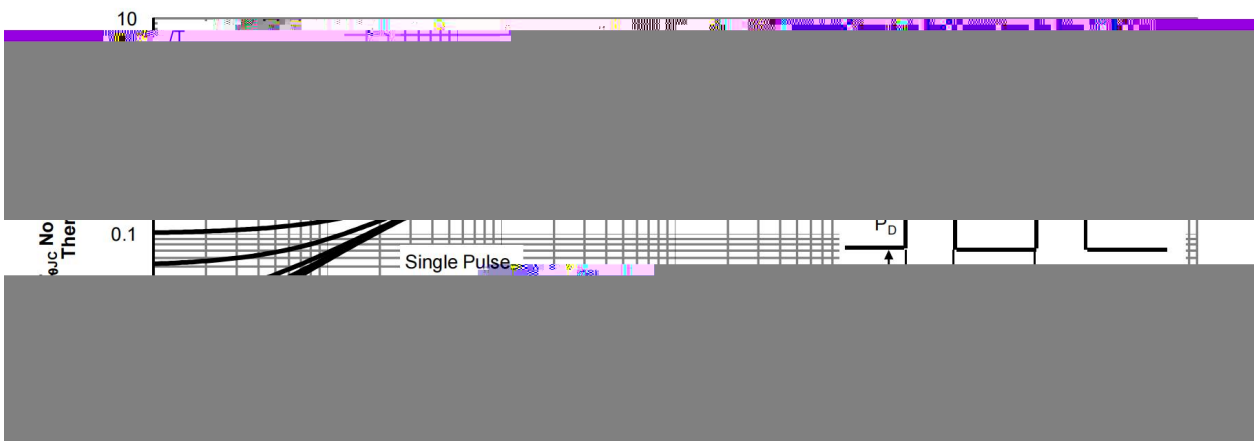
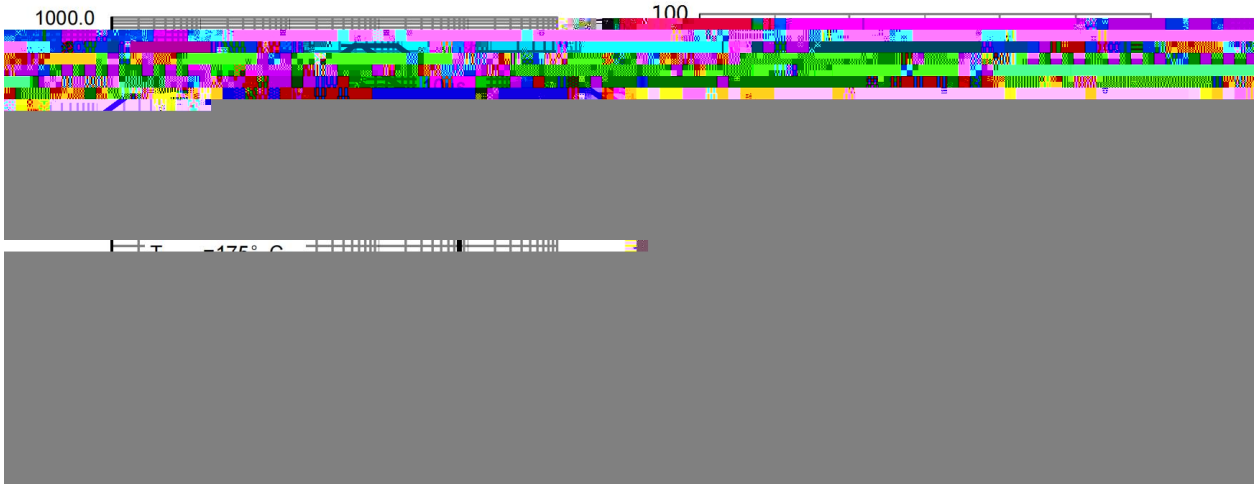
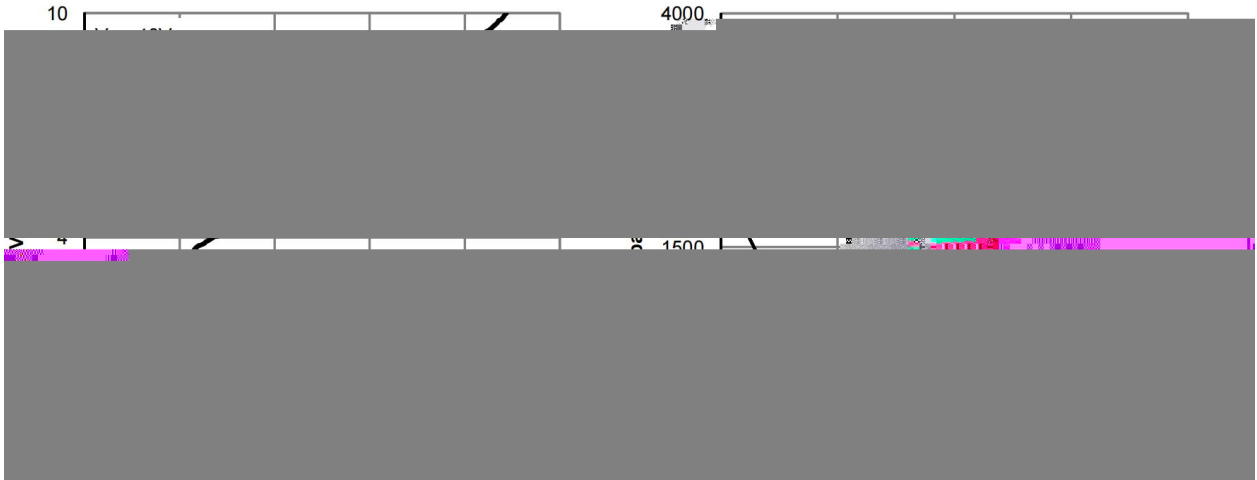
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Gate resistance	R_g	$f=1\text{MHz}$		1.6		Ω
Total Gate Charge	$Q_g(10\text{V})$	$V_{GS}=10\text{V}$ $V_{DS}=40\text{V}$ $I_D=20\text{A}$		44.5		nC
Gate Source Charge	Q_{gs}			12		
Gate Drain Charge	Q_{gd}			8		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10\text{V}$ $V_{DS}=40\text{V}$ $R_L=2\Omega$ $R_{GEN}=3\Omega$		13.5		ns
Turn-On Rise Time	t_r			11		
Turn-Off Delay Time	$t_{d(off)}$			32		
Turn-Off Fall Time	t_f			11		

/ Electrical Characteristic Curve



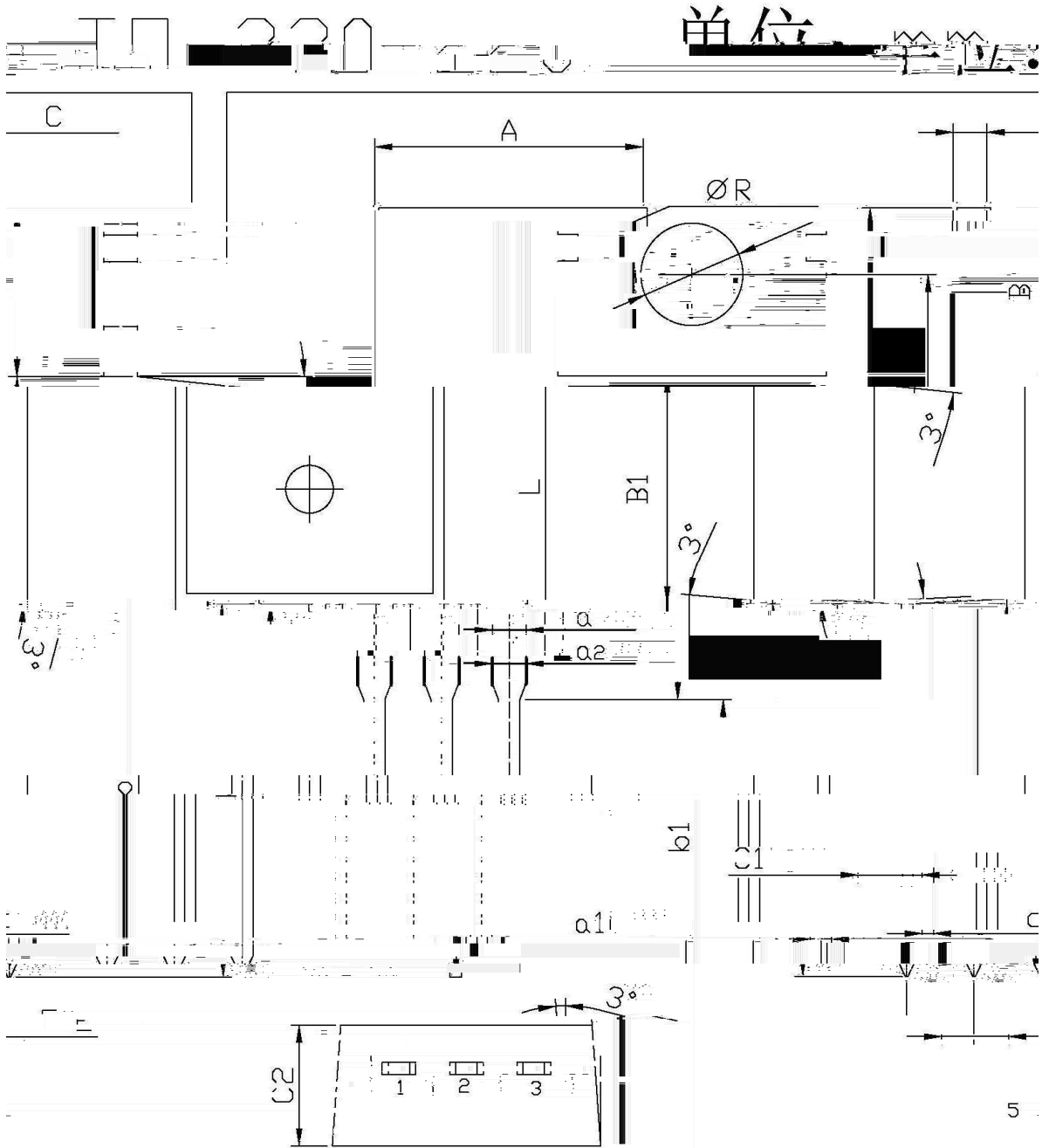


/ Electrical Characteristic Curve



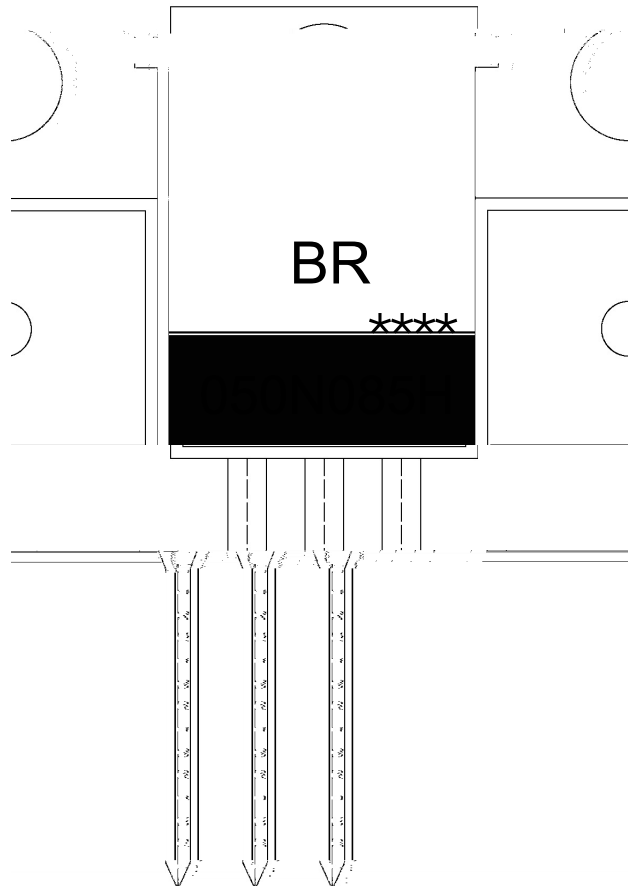


/ Package Dimensions



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
Δ	9.8	10.2	C	12	14
R	3.56	3.64	B	6.3	6.7
	15.7	16.1	B1	9.0	9.4
	13.6	13.6	C1	2.2	2.5
	9.6	10.6	a1	0.7	0.9
	1.22	1.22	a2	0.4	0.6
	1.234	1.274	b1	4.3	4.7
			a2	1.25	1.45

/ Marking Instructions



说明：

BR： 为公司代码

050N085H： 为型号代码

****： 为生产批号代码，随生产批号变化。

Note:

BR: Company Code

050N085H: Product Type.

****: Lot No. Code, code change with Lot No.

BRCS050N085HRA

Rev.A Sep.-2021



DATA SHEET

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